

One Watt High Current Transistors

PNP Silicon

- These devices are available in Pb-free package(s). Specifications herein apply to both standard and Pb-free devices. Please see our website at www.onsemi.com for specific Pb-free orderable part numbers, or contact your local ON Semiconductor sales office or representative.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emmitter Voltage MPSW51 MPSW51A	V_{CEO}	-30 -40	Vdc
Collector-Base Voltage MPSW51 MPSW51A	V_{CBO}	-40 -50	Vdc
Emitter-Base Voltage	V_{EBO}	-5.0	Vdc
Collector Current — Continuous	I_C	-1000	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	1.0 8.0	Watts mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	2.5 20	Watts mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	125	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

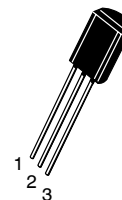
Collector-Emmitter Breakdown Voltage ⁽¹⁾ ($I_C = -1.0 \text{ mAdc}, I_E = 0$)	MPSW51 MPSW51A	$V_{(BR)CEO}$	-30 -40	— —	Vdc
Collector-Base Breakdown Voltage ($I_C = -100 \mu\text{Adc}, I_E = 0$)	MPSW51 MPSW51A	$V_{(BR)CBO}$	-40 -50	— —	Vdc
Emitter-Base Breakdown Voltage ($I_E = -100 \mu\text{Adc}, I_C = 0$)		$V_{(BR)EBO}$	-5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = -30 \text{ Vdc}, I_E = 0$) ($V_{CB} = -40 \text{ Vdc}, I_E = 0$)	MPSW51 MPSW51A	I_{CBO}	— —	-0.1 -0.1	μAdc
Emitter Cutoff Current ($V_{EB} = -3.0 \text{ Vdc}, I_C = 0$)		I_{EBO}	—	-0.1	μAdc

1. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

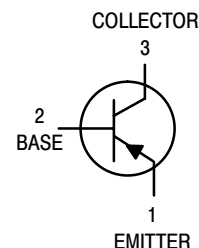
Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

MPSW51 MPSW51A*

*ON Semiconductor Preferred Device



CASE 29-10, STYLE 1
TO-92 (TO-226AE)



MPSW51 MPSW51A

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS				
DC Current Gain ($I_C = -10\text{ mAdc}$, $V_{CE} = -1.0\text{ Vdc}$) ($I_C = -100\text{ mAdc}$, $V_{CE} = -1.0\text{ Vdc}$) ($I_C = -1000\text{ mAdc}$, $V_{CE} = -1.0\text{ Vdc}$)	h_{FE}	55 60 50	—	—
Collector–Emitter Saturation Voltage ($I_C = -1000\text{ mAdc}$, $I_B = -100\text{ mAdc}$)	$V_{CE(sat)}$	—	-0.7	Vdc
Base–Emitter On Voltage ($I_C = -1000\text{ mAdc}$, $V_{CE} = -1.0\text{ Vdc}$)	$V_{BE(on)}$	—	-1.2	Vdc
SMALL–SIGNAL CHARACTERISTICS				
Current–Gain – Bandwidth Product ($I_C = -50\text{ mAdc}$, $V_{CE} = -10\text{ Vdc}$, $f = 20\text{ MHz}$)	f_T	50	—	MHz
Output Capacitance ($V_{CB} = -10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{obo}	—	30	pF

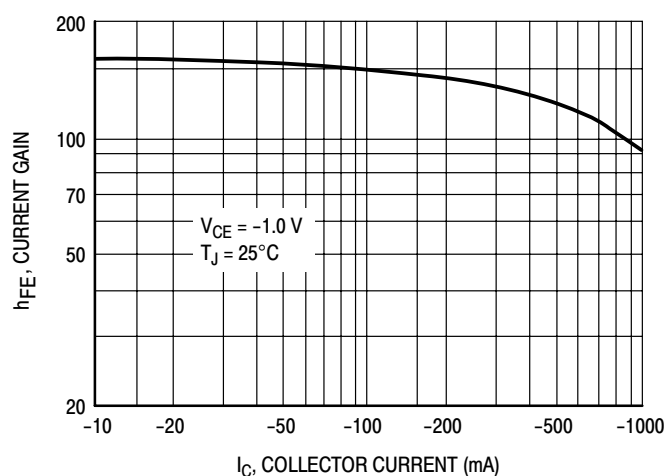


Figure 1. DC Current Gain

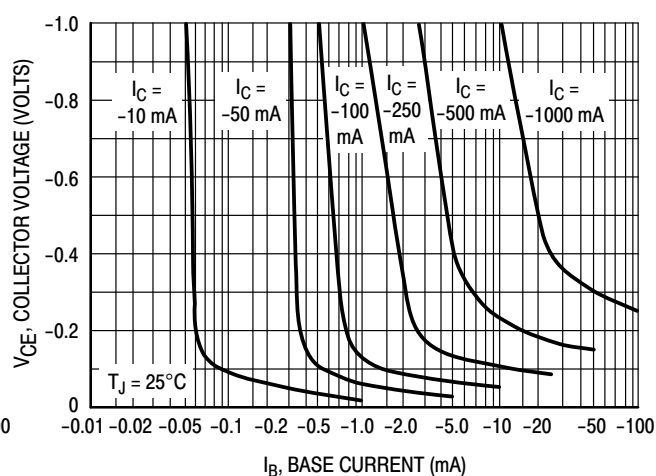


Figure 2. Collector Saturation Region

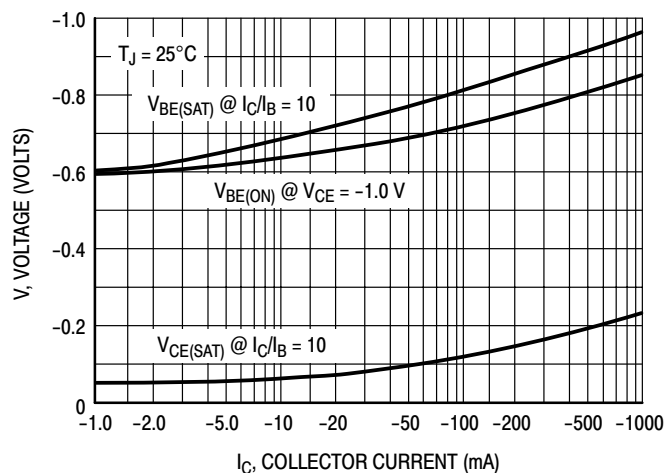


Figure 3. "ON" Voltages

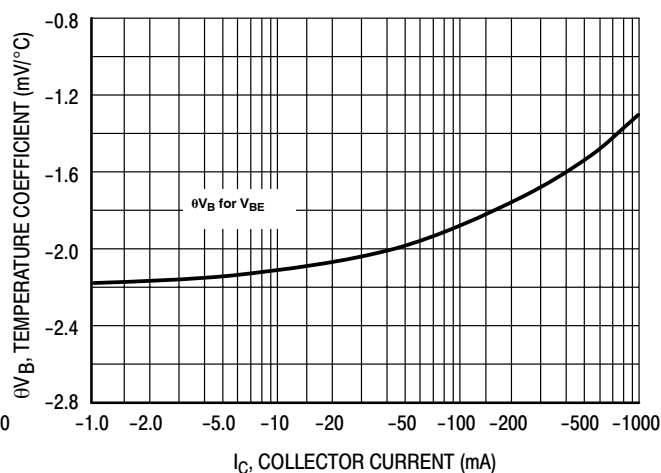


Figure 4. Temperature Coefficient

MPSW51 MPSW51A

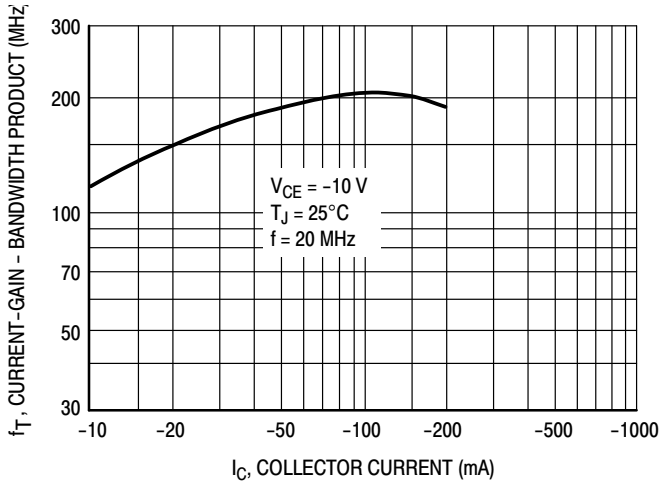


Figure 5. Current Gain — Bandwidth Product

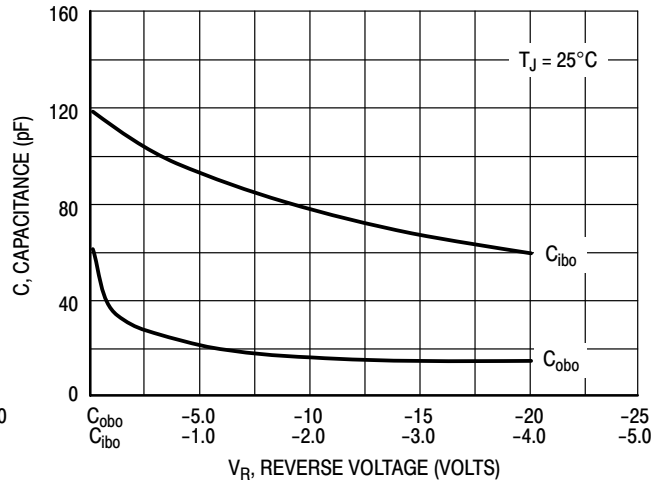


Figure 6. Capacitance

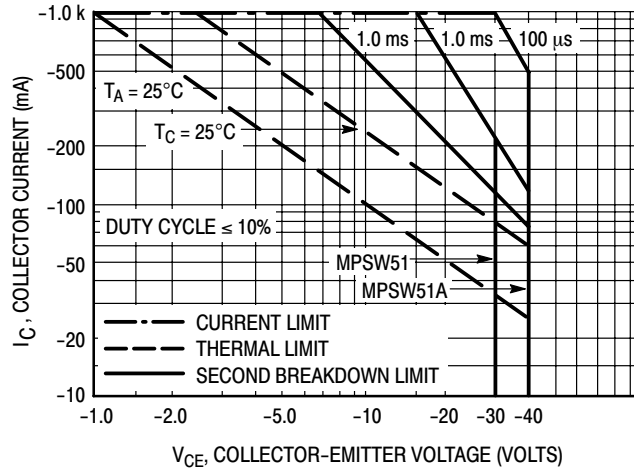
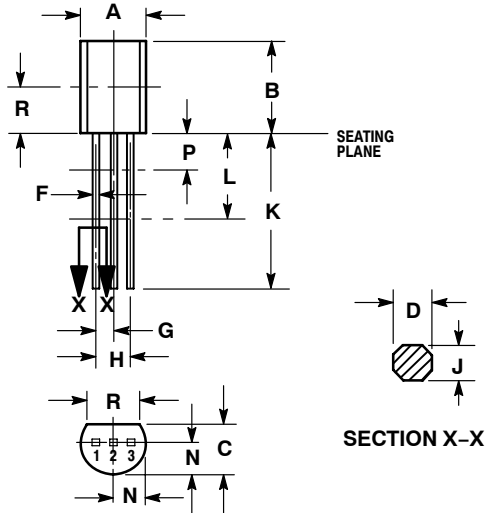


Figure 7. Active Region — Safe Operating Area

MPSW51 MPSW51A

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-10 ISSUE AL



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSIONS D AND J APPLY BETWEEN L AND K MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.44	5.21
B	0.290	0.310	7.37	7.87
C	0.125	0.165	3.18	4.19
D	0.018	0.021	0.457	0.533
F	0.016	0.019	0.407	0.482
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.018	0.024	0.46	0.61
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.135	---	3.43	---

STYLE 1:

1. EMITTER
2. BASE
3. COLLECTOR

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